

- AVAILABLE IN JAN, JANTX AND JANTXV
PER MIL-PRF-19500/118
- GENERAL PURPOSE SILICON DIODES
- METALLURGICALLY BONDED

1N5194UR
1N5195UR
1N5196UR
CDLL5194
CDLL5195
CDLL5196

MAXIMUM RATINGS

Operating Temperature: -65°C to +175°C
Storage Temperature: -65°C to +175°C
Operating Current: 200 mA
Derating: 1.2mA/°C from 25°C to 150°C
1.0mA/°C from 150°C to 175°C
Forward Current: 650mA

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V_{RM}	V_{RWM}	I_O	I_O $T_A = +150^\circ C$	I_{FSM} $T_p=1/120 S$ $T_A=25^\circ C$
	$V_{(pk)}$	$V_{(pk)}$	mA	mA	A
CDLL, 1N5194UR	80	70	200	50	2
CDLL, 1N5195UR	180	180	200	50	2
CDLL, 1N5196UR	250	225	200	50	2

TYPE	V_F @100mA	I_{R1} at V_{RWM}	I_{R2} at V_{RM} $T_A=25^\circ C$	I_{R3} at V_{RWM} $T_A = 150^\circ C$
	V dc	nA dc	μA	μA dc
CDLL, 1N5194UR	0.8 - 1.0	25	100	5
CDLL, 1N5195UR	0.8 - 1.0	25	100	5
CDLL, 1N5196UR	0.8 - 1.0	25	100	5

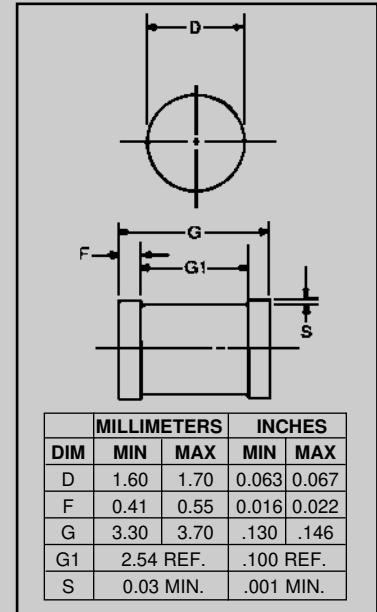


FIGURE 1

DESIGN DATA

CASE: DO-213AA, Hermetically sealed glass case. (MELF, SOD-80, LL34)

LEAD FINISH: Tin / Lead

THERMAL RESISTANCE: (R_{QJEC}): 100 °C/W maximum

THERMAL IMPEDANCE: (Z_{QJX}): 70 °C/W maximum

POLARITY: Cathode end is banded.

MOUNTING POSITION: Any.

MOUNTING SURFACE SELECTION:

The Axial Coefficient of Expansion (COE) Of this Device is Approximately +6PPM/°C. The COE of the Mounting Surface System Should Be Selected To Provide A Suitable Match With This Device.



IN5194UR thru IN5196UR, CDLL5194 thru CDLL5196

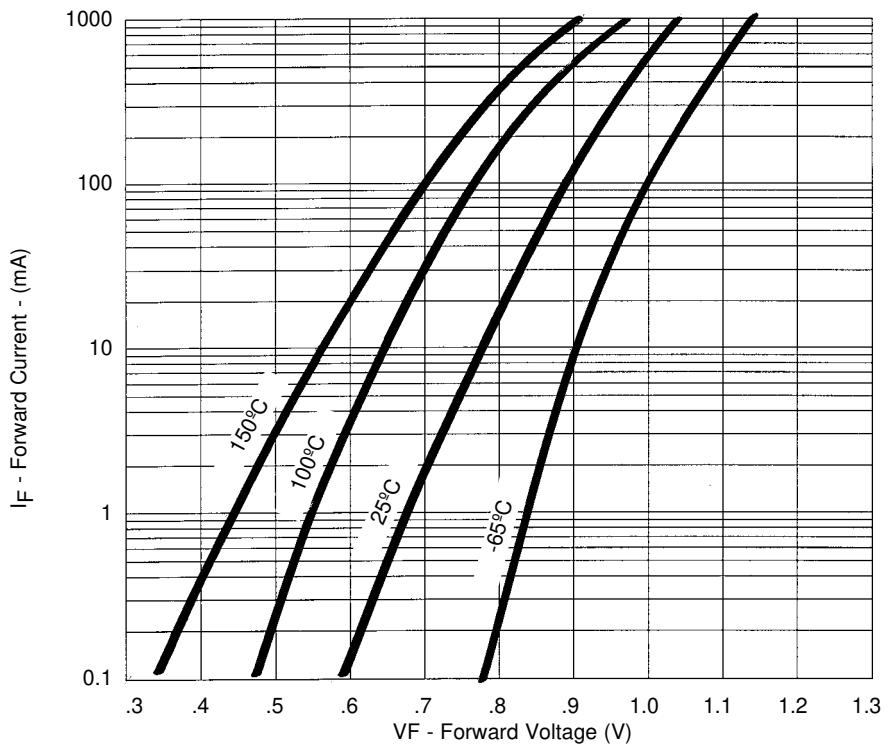
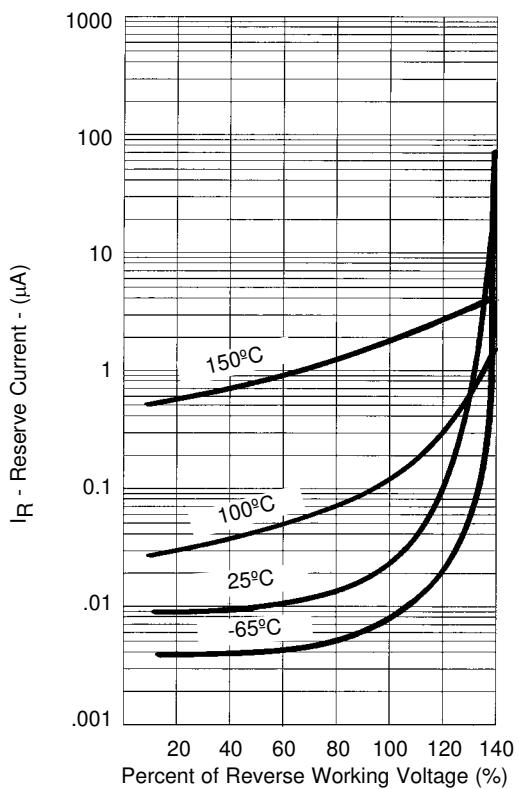


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage